

isc Silicon PNP Power Transistor

2SB760

DESCRIPTION

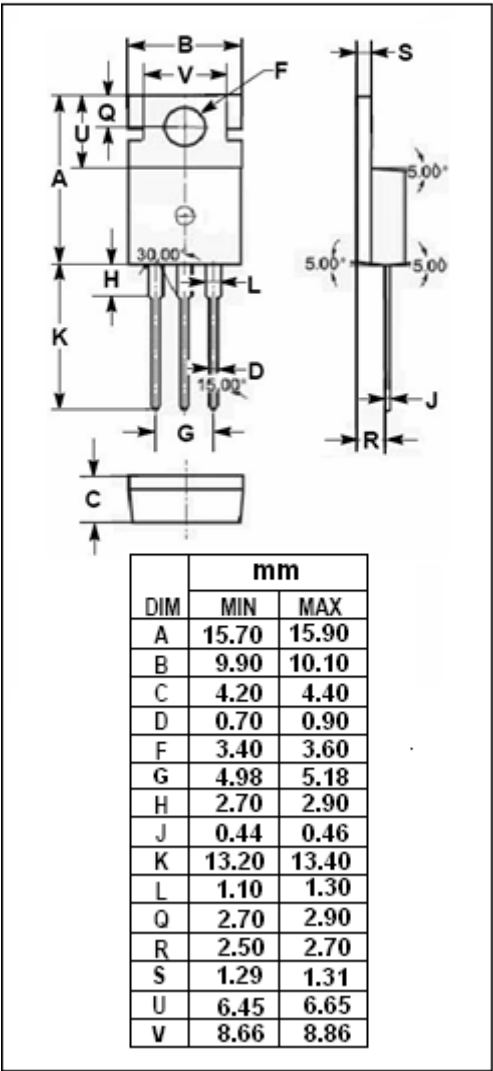
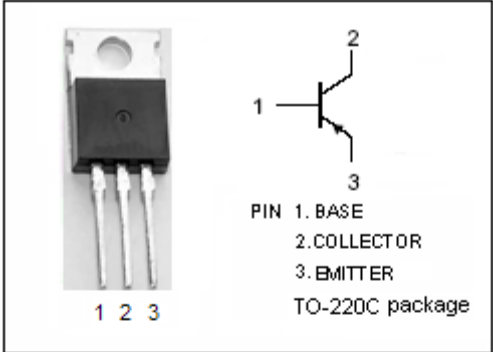
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -60V(\text{Min})$
- Good Linearity of h_{FE}
- Wide Area of Safe Operation
- Complement to Type 2SD855

APPLICATIONS

- Medium power amplifier applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1	A
I_{CM}	Collector Current-Peak	-2	A
P_C	Collector Power Dissipation @ $T_C=25^{\circ}\text{C}$	30	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon PNP Power Transistor**2SB760****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -30\text{mA}$; $I_B = 0$	-60			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -1\text{A}$; $I_B = -0.125\text{A}$			-1.0	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -1\text{A}$; $V_{CE} = -4\text{V}$			-1.3	V
I_{CEO}	Collector Cutoff Current	$V_{CE} = -60\text{V}$; $I_B = 0$			-300	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -5\text{V}$; $I_C = 0$			-1	mA
h_{FE-1}	DC Current Gain	$I_C = -0.2\text{A}$; $V_{CE} = -4\text{V}$	40		250	
h_{FE-2}	DC Current Gain	$I_C = -1\text{A}$; $V_{CE} = -4\text{V}$	15			

◆ **h_{FE-1} Classifications**

R	Q	P
40-90	70-150	120-250